

Supporting Information

Effects of Self-Assembled Monolayer Modification of Nickel Oxide Nanoparticles Layer on the Performance and Application of Inverted Perovskite Solar Cells

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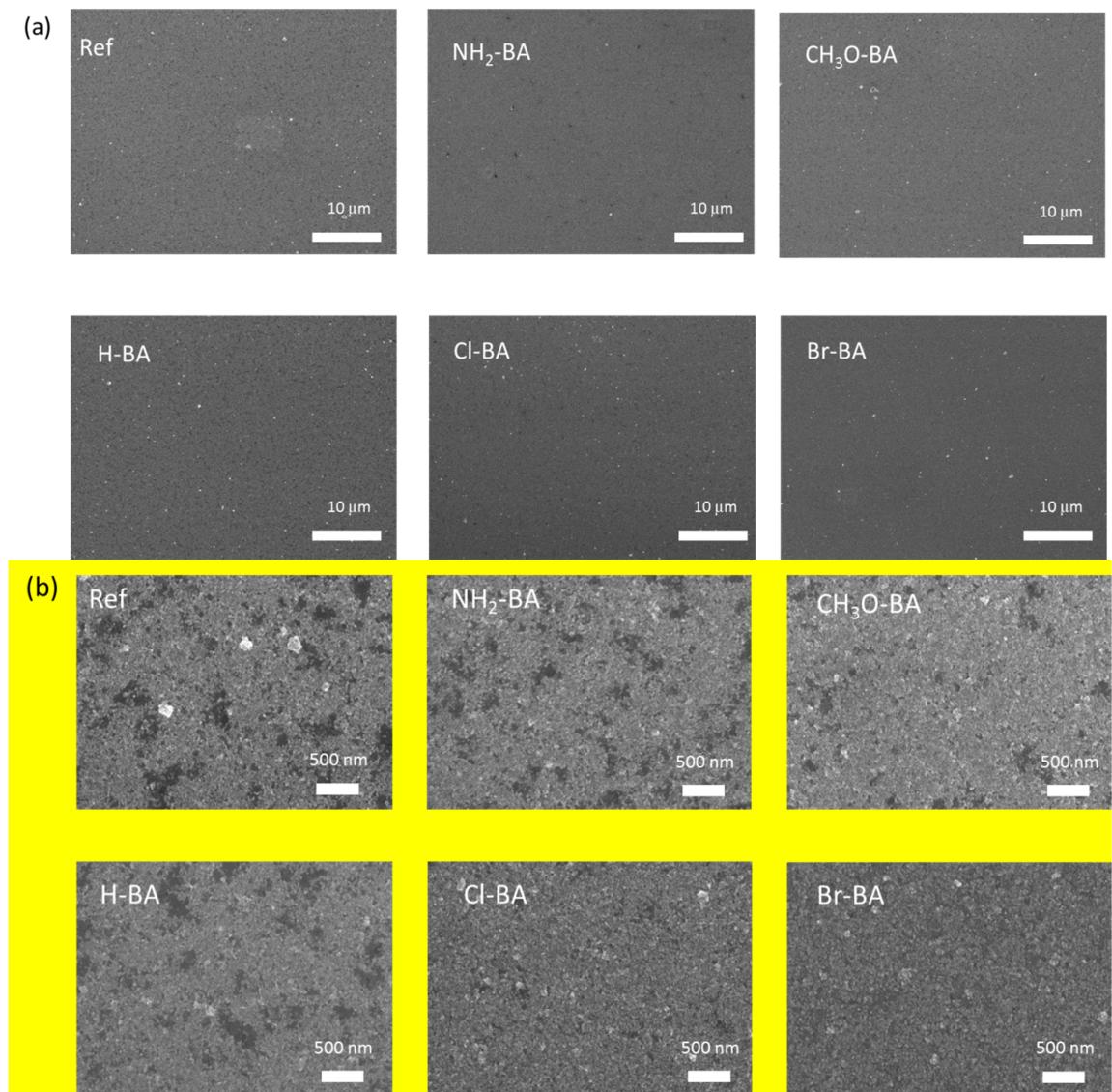


Figure S1. SEM images of NiO_x films with different SAMs at magnification of (a) 2500 times and (b) 20000 times.

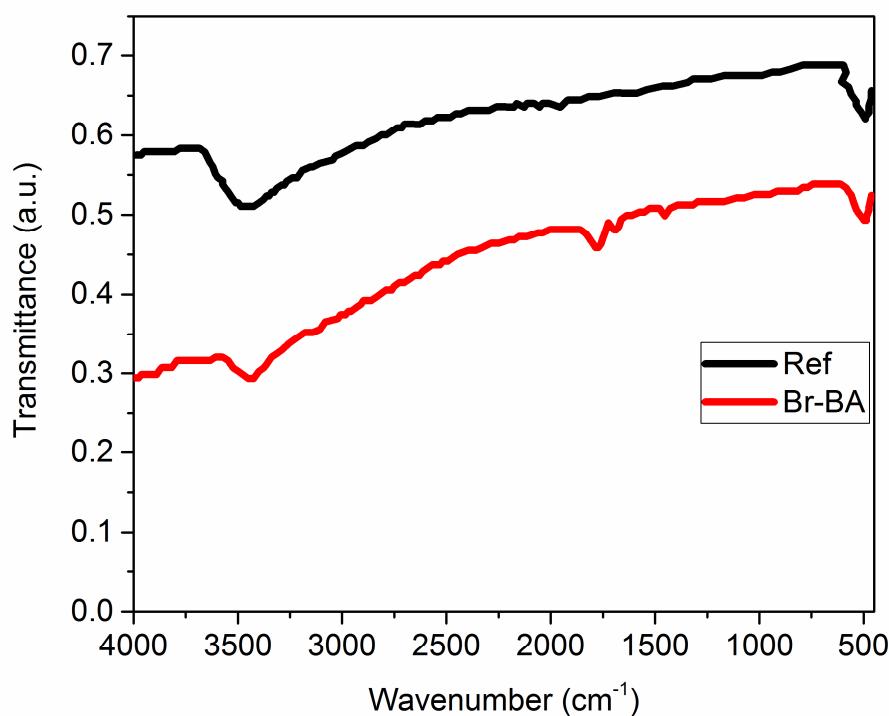


Figure S2. FTIR spectra of NiO_x without and with Br-BA modification. From the FTIR spectrum, the Ref group has a strong peak at 3450 cm^{-1} which is attributed to the O-H stretching vibration. After Br-BA modification, the peak at 3450 cm^{-1} becomes weaker demonstrating the reaction of carboxyl functional group of Br-BA and hydroxyl functional group of NiO_x . Also, the new appearing peak ranging from $1700\text{-}1500 \text{ cm}^{-1}$ corresponds to the aromatic C=C bending peaks, which comes from the Br-BA.

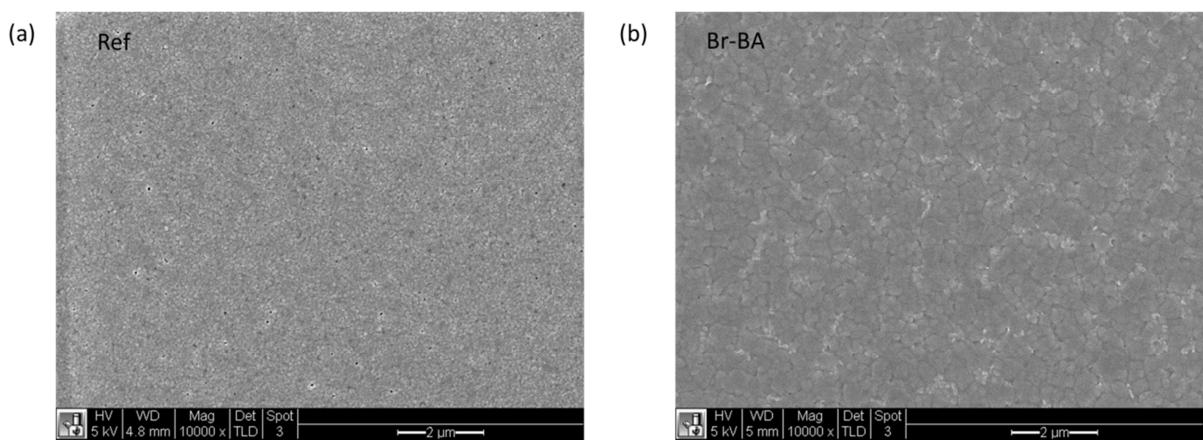


Figure S3. Large view of surface morphology of (a) Ref and (b) Br-BA modified NiO_x films. Scale bar is $2 \mu\text{m}$.

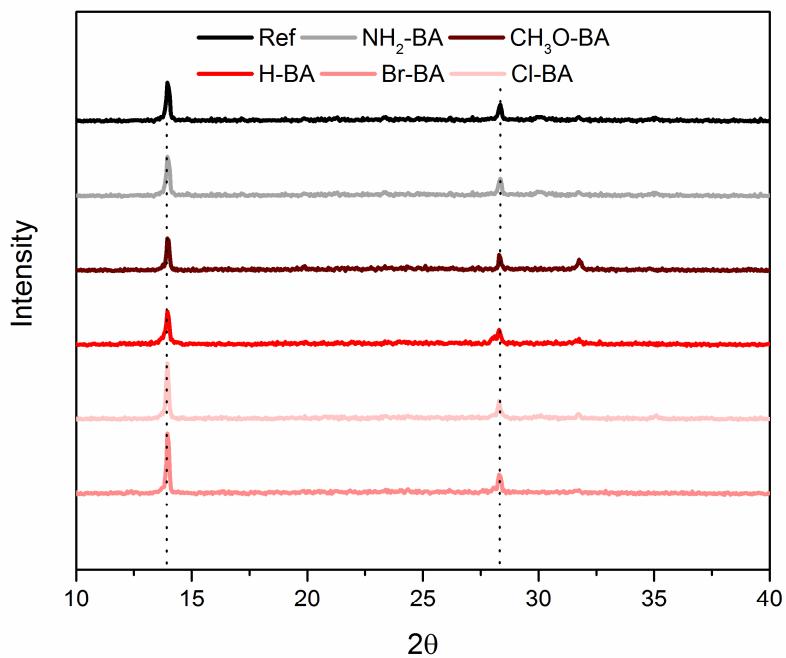


Figure S4. XRD patterns of the MAPbI_3 perovskite films deposited on various R-BA modified NiO_x films spun on glass substrates.

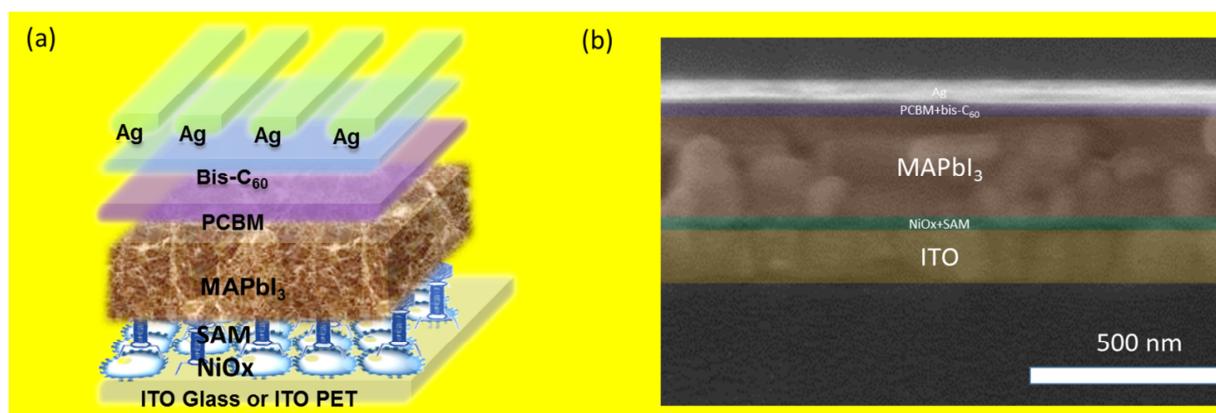


Figure S5. (a) Device structure of the PVSCs made in this study; (b) Cross section image of ITO/NiO_x/SAM/MAPbI₃/PCBM/bisC₆₀/Ag

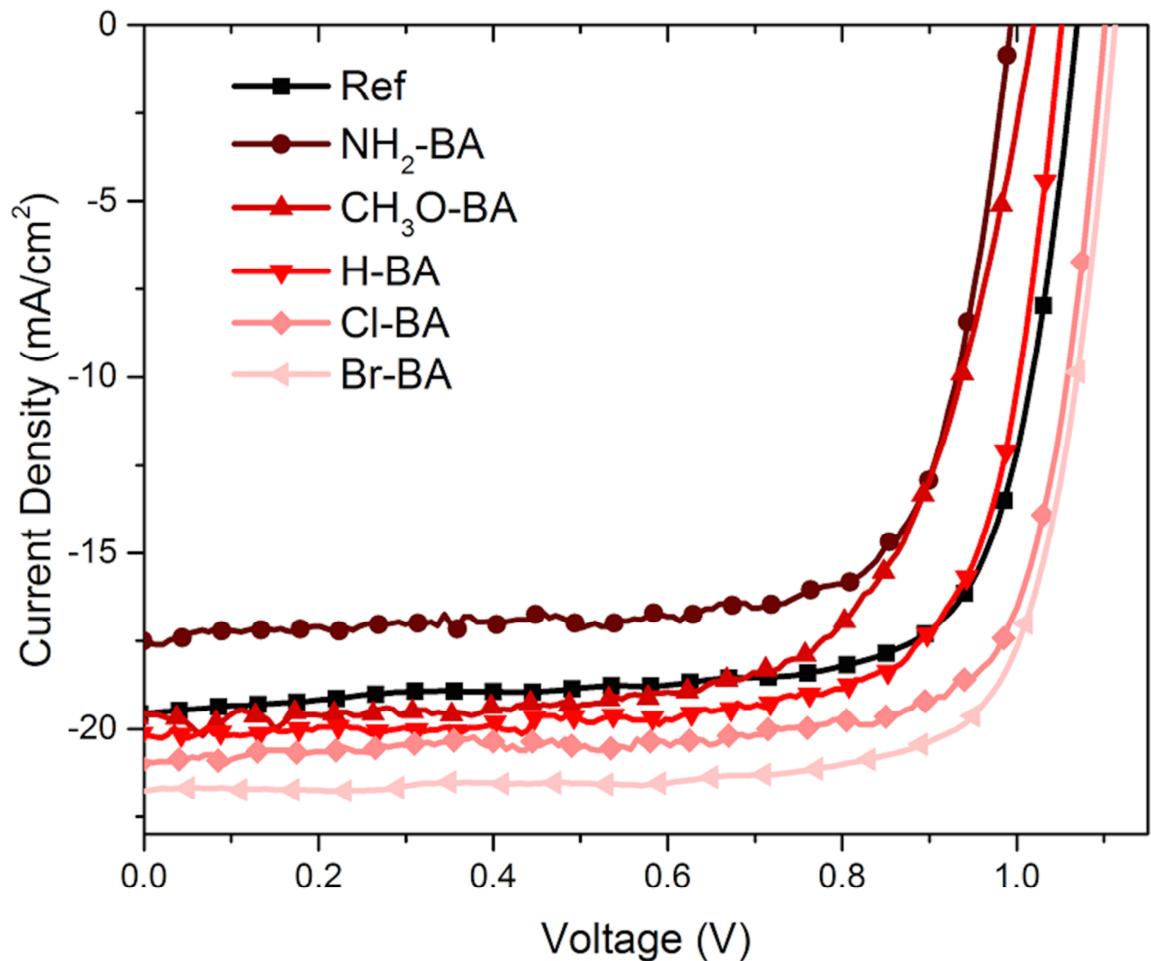


Figure S6: J-V curves of PVSC with and without SAM modification.

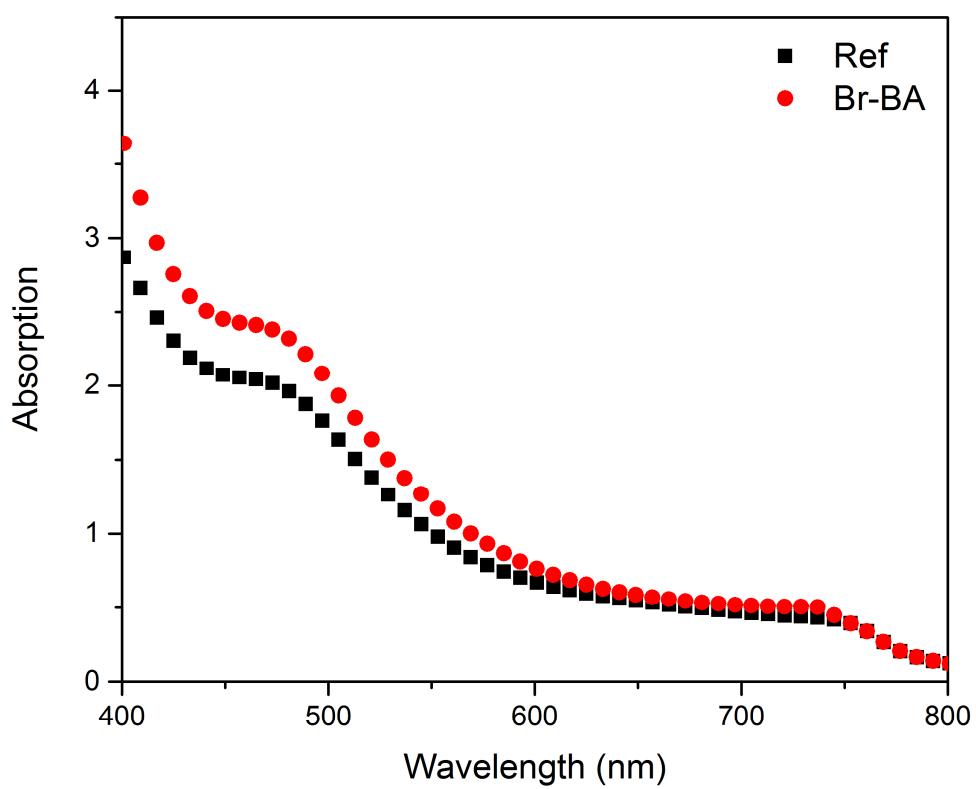


Figure S7. Absorption spectrum of the PVSCs with and without Br-BA modification.

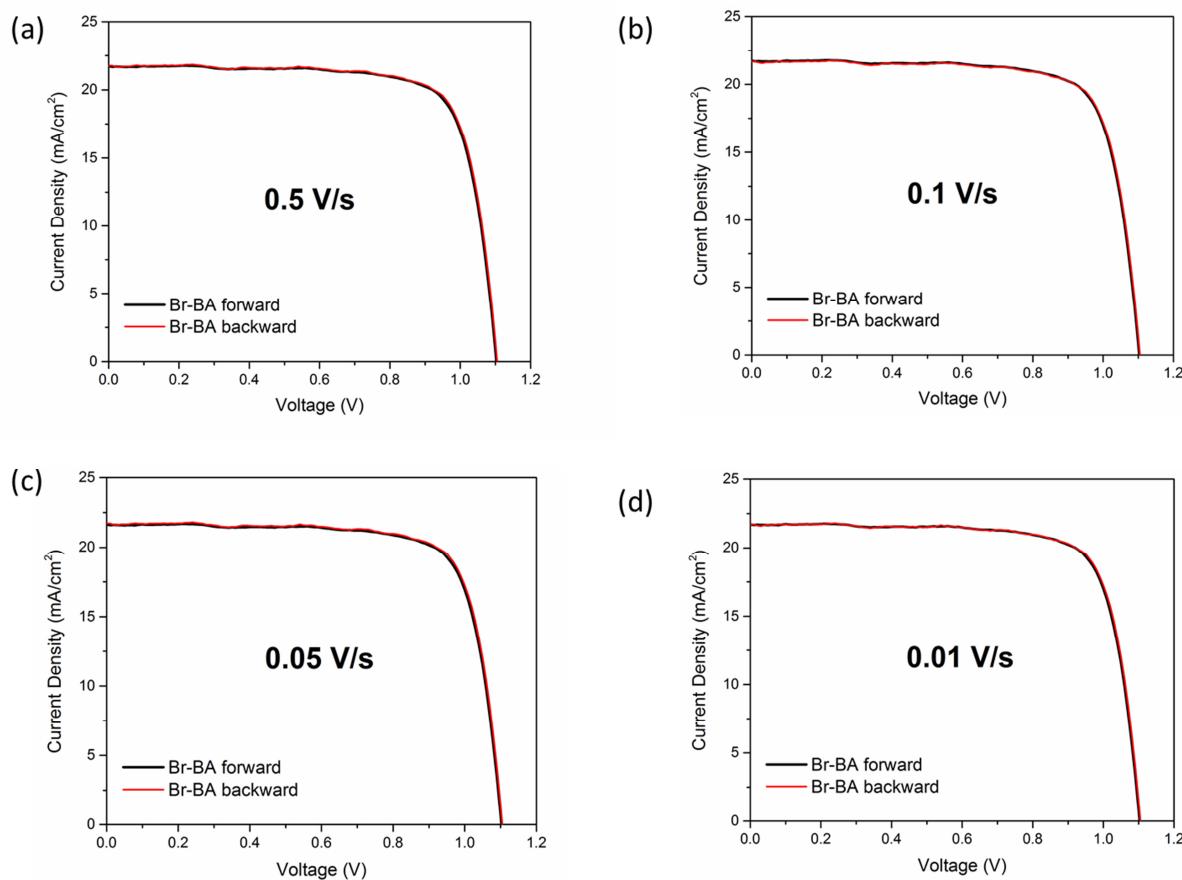


Figure S8. J-V curves of the Br-BA modified PVSCs at various scan rates: (a) 0.5, (b) 0.1, (c) 0.05, and (d) 0.01 V s⁻¹.

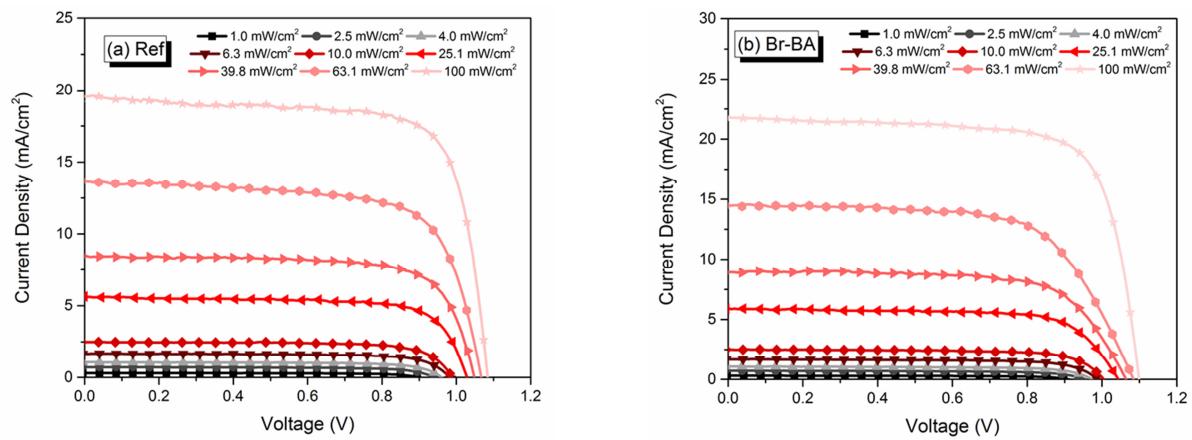


Figure S9. J-V curves of (a) the Ref and (b) Br-BA modified PVSCs at various light intensities.

Table S1. Photovoltaic parameters of various SAM-modified PVSCs.

| SAMs | V _{oc} | J _{sc} | FF (%) | PCE (%) |
|-------------------|-----------------|-----------------|--------|---------|
| None | 1.07 | 19.6 | 74.2 | 15.5 |
| -NH ₂ | 0.99 | 17.5 | 74.1 | 12.8 |
| -OCH ₃ | 1.02 | 19.1 | 70.6 | 13.8 |
| -H | 1.05 | 20.3 | 76.2 | 16.2 |
| -Cl | 1.10 | 21.0 | 76.0 | 17.6 |
| -Br | 1.11 | 21.7 | 76.3 | 18.4 |
| -Br on ITO/PET | 1.10 | 20.7 | 71.3 | 16.2 |

Table S2. Summary of the recent works focusing on the application of NiO_x HTL in PVSCs

| Device structure | V_{oc} (V) | J_{sc} (mA/cm ²) | FF (%) | PCE (%) | High T ^{a)} | Reference |
|--|--------------|--------------------------------|--------|---------|----------------------|-----------|
| ITO/ NiO_x (solution)/ $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ Al | 1.05 | 15.4 | 47 | 7.6 | Y (300 °C) | [1] |
| ITO/ NiO_x (solution)/ NiO_{nc} / $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ BCP/ Al | 1.04 | 13.2 | 69 | 9.5 | Y (300 °C) | [2] |
| FTO/ NiO_x (sol-gel)/ $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ Au | 0.88 | 16.3 | 64 | 9.1 | Y (500 °C) | [3] |
| ITO/ NiO_x (sputtered)/ NiO_{nc} / $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ BCP/ Al | 0.96 | 19.8 | 61 | 11.6 | Y (400 °C) | [4] |
| FTO/ NiO_x (spray pyrolysis)/ meso- Al_2O_3 / $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ BCP/ Ag | 1.04 | 18.0 | 72 | 13.5 | Y (500 °C) | [5] |
| ITO/ Cu: NiO_x (sol-gel)/ $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ bis-C ₆₀ / Ag | 1.11 | 19.0 | 73 | 15.4 | Y (400 °C) | [6] |
| FTO/ NiO_x (sputtered)/ NiO_{nc} / $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ BCP/ Au | 1.10 | 15.2 | 59 | 9.83 | Y (450 °C) | [7] |
| ITO/ NiO_x (PLD)/ $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ LiF/ Al | 1.06 | 20.2 | 81 | 17.3 | N (150 °C) | [8] |
| ITO/ Cu: NiO_x (combustion)/ $\text{CH}_3\text{NH}_3\text{PbI}_3$ / C ₆₀ / bis-C ₆₀ / Ag | 1.05 | 22.2 | 76 | 17.8 | N (150 °C) | [9] |
| FTO/ NiO_x (Li:Mg) (spray pyrolysis)/ $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ Ti(Nb)O _x / Ag | 1.09 | 20.4 | 83 | 18.4 | Y (500 °C) | [10] |
| ITO/ NiO_x (sol-gel)/ DEA/ $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$ / PCBM/ Ag | 0.95 | 20.9 | 80 | 15.9 | Y (500 °C) | [11] |
| ITO/ NiO_x (solution)/ $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ PDINO/ Ag | 1.11 | 20.57 | 76.5 | 17.5 | N (140 °C) | [12] |
| ITO/ NiO_x (NPs)/ $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ Ag | 1.07 | 20.58 | 74.8 | 16.5 | N (130 °C) | [13] |
| ITO/ NiO_x (sol-gel)/ $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ Ag | 1.09 | 19.9 | 76.9 | 16.7 | Y (300 °C) | [14] |
| ITO/ NiO_x (NPs)/ $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ bis-C ₆₀ / Ag | 1.03 | 21.8 | 78.4 | 17.6 | N (25 °C) | [15] |
| ITO/ NiO_x (NPs)/ $\text{CH}_3\text{NH}_3\text{PbI}_3$ / C ₆₀ / bis-C ₆₀ / Ag | 1.05 | 22.6 | 72.1 | 17.1 | N (25 °C) | [16] |
| ITO/ NiO_x (NPs)/ $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ BCP / Ag | 1.03 | 20.66 | 74.2 | 15.9 | N (25 °C) | [17] |
| FTO/ Cs: NiO_x (sol-gel)/ $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ Zr(Acac)/ Ag | 1.12 | 21.77 | 79.3 | 19.35 | Y (275 °C) | [18] |
| ITO/ NiO_x (NPs)/ SAM/ $\text{CH}_3\text{NH}_3\text{PbI}_3$ / PCBM/ bis-C ₆₀ / Ag | 1.11 | 21.7 | 76.3 | 18.4 | N (25 °C) | This work |

^{a)} High T denotes high temperature processed NiO_x films, which are not compatible with the roll-to-roll fabrication.

Table S3. Summary of the recent works of low-temperature processed NiO_x film based flexible perovskite solar cells (F-PVSCs) with PCE $\geq 10\%$ made on PET substrate.

| Device structure | V _{oc} (V) | J _{sc} | FF (%) | PCE (%) | Power per weight (W/g) | Reference |
|--|---------------------|-----------------------|--------|---------|------------------------|-----------|
| | | (mA/cm ²) | | | | |
| ITO/ NiO _x (NPs)/ CH ₃ NH ₃ PbI ₃ / C ₆₀ / bis-C ₆₀ / Ag | 0.997 | 20.7 | 70.5 | 14.5 | / | [15] |
| ITO/ NiO _x (NPs)/ CH ₃ NH ₃ PbI ₃ / PCBM/ BCP / Ag | 1.04 | 17.44 | 64.2 | 11.84 | / | [17] |
| ITO/ NiO _x (PLD)/ CH ₃ NH ₃ PbI ₃ / PCBM/ LiF/ Al | 1.04 | 18.7 | 68.9 | 13.4 | / | [13] |
| ITO/ NiO _x (NPs)/ CH ₃ NH ₃ PbI ₃ / PCBM/ PDINO/ Ag | 0.975 | 20.9 | 69.63 | 14.19 | 23.26 | [16] |
| ITO/ NiO _x (NPs)/ SAM/ CH ₃ NH ₃ PbI ₃ / PCBM/ bis-C ₆₀ / Ag | 1.1 | 20.7 | 71.3 | 16.2 | 26.92 | This work |

Table S4. Calculation of power per weight (w/g)

| Materials | Thickness | Weight (g/m ²) | Power |
|--------------------------|-----------|----------------------------|---|
| PET/ITO | 1.4 μm | 5.6 | |
| NiO _x | 20 nm | 1.5×10 ⁻⁴ | |
| MAPbI ₃ | 250 nm | 0.4167 | (one-sun)1000W/m ² ×PCE = 1000×16.2% W/m ² = 162 W/m ² |
| PCBM/bis-C ₆₀ | 40 nm | 8.34×10 ⁻⁵ | |
| Ag | 120 nm | 1.26×10 ⁻³ | |
| Total | | 6.0182 | |

Therefore, the power per weight of F-PVSC= 162÷ 6.0182= 26.92 W/g

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